

L Number	Hits	Search Text	DB	Time stamp
2	22374	"Chemical mechanical polishing" or CMP	USPAT; EPO; JPO; DERWENT; IBM TDB	2002/09/25 15:41
3	125	(("silicon dioxide" or "SiO.sub.2") same ("silicon nitride" or SiN) same sacrific\$3) and ("Chemical mechanical polishing" or CMP)	USPAT; EPO; JPO; DERWENT; IBM TDB	2002/09/25 15:41
1	388	("silicon dioxide" or "SiO.sub.2") same ("silicon nitride" or SiN) same sacrific\$3	USPAT; EPO; JPO; DERWENT; IBM TDB	2002/09/25 16:46
6	708	("Chemical mechanical polishing" or CMP) same sacrific\$3	USPAT; EPO; JPO; DERWENT; IBM TDB	2002/09/25 16:44
7	557	(resist or photoresist or mask) same redeposit\$4	USPAT; EPO; JPO; DERWENT; IBM TDB	2002/09/25 16:45
9	8314	(resist or photoresist or mask) same (redeposit\$4 or veil or residual)	USPAT; EPO; JPO; DERWENT; IBM TDB	2002/09/25 16:53
10	2847	("silicon dioxide" or "SiO.sub.2") and ("silicon nitride" or SiN) and sacrific\$3	USPAT; EPO; JPO; DERWENT; IBM TDB	2002/09/25 16:47
11	38	("Chemical mechanical polishing" or CMP) and ((resist or photoresist or mask) same (redeposit\$4 or veil or residual)) and ((("silicon dioxide" or "SiO.sub.2") and ("silicon nitride" or SiN) and sacrific\$3) (resist or photoresist or mask) same sidewall same (redeposit\$4 or veil or residual)	USPAT; EPO; JPO; DERWENT; IBM TDB	2002/09/25 16:47
12	279		USPAT; EPO; JPO; DERWENT; IBM TDB	2002/09/25 16:53